Claims:

1. A linear device including a gate electrode, a gate insulating region, a source region, a drain region, and a semiconductor region, characterized in

that said semiconductor region is arranged between said source region comprising one or a plurality of source region(s) and said drain region comprising one or a plurality of drain region(s), in a radial direction within a cross section of a device region, so that a part of said gate insulating region is contacted with said semiconductor region.

2. The linear device of claim 1, wherein said gate electrode and said gate insulating region are arranged inside or outside said source region(s) and said drain region(s).

3. The linear device of claim 1 or 2, wherein said linear device comprises, at a center, one of: a hollow region; an electric conductor region; said gate electrode; said source region; said drain region; another insulating region different from said gate insulating region; and another semiconductor region different from said semiconductor region.

4. The linear device of any one of claims 1 through 3, wherein said linear device comprises a plurality of device regions through separation regions therebetween, respectively, in a longitudinal direction of a linear body constituting said linear device.

5. The linear device of any one of claims 1 through 4, wherein said gate electrode, gate insulating region, source region(s), drain region(s), and/or semiconductor region constituting said linear device are formed of an organic semiconductor or electroconductive polymer.